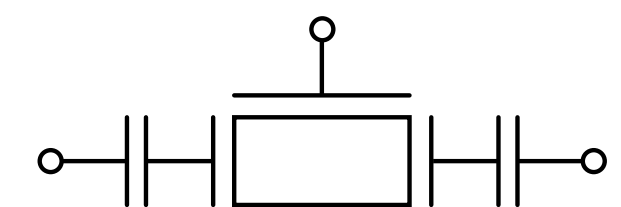
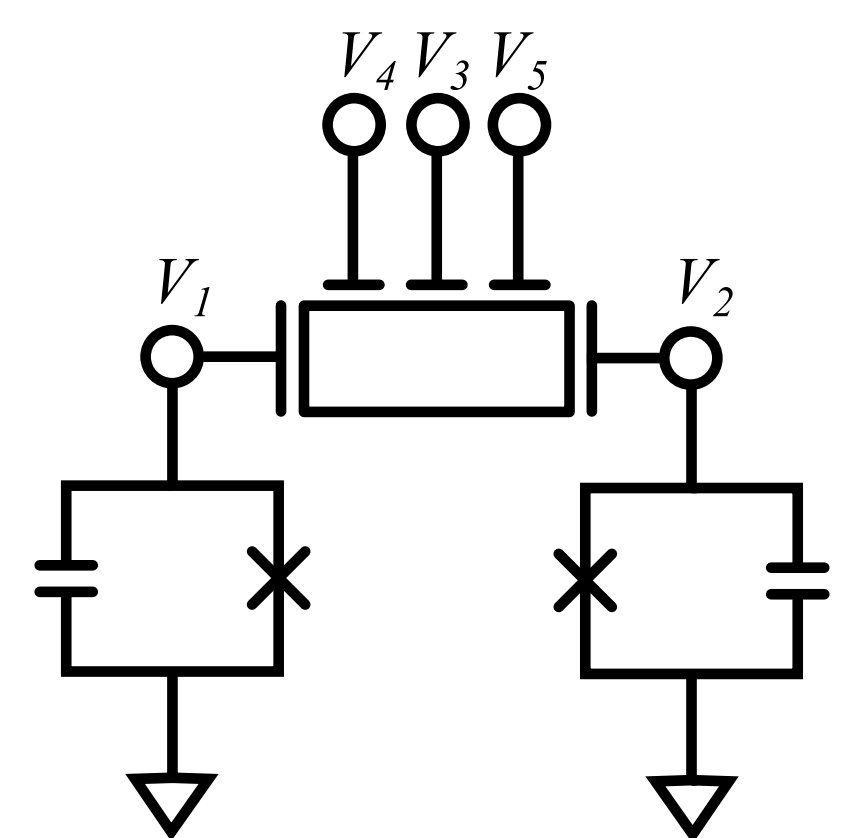


Voltage vs. Flux Biased Couplers

Voltage-controlled coupler

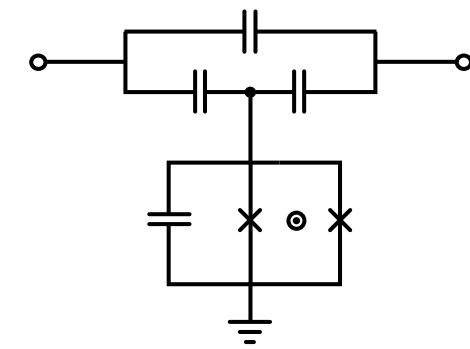


- + 2nd order sensitive to voltage bias
- + No heating introduced by voltage bias
- + Minimal cross-talk expected
- Not part of cQED fab, yet
- Dielectric loss from 2DEG possible



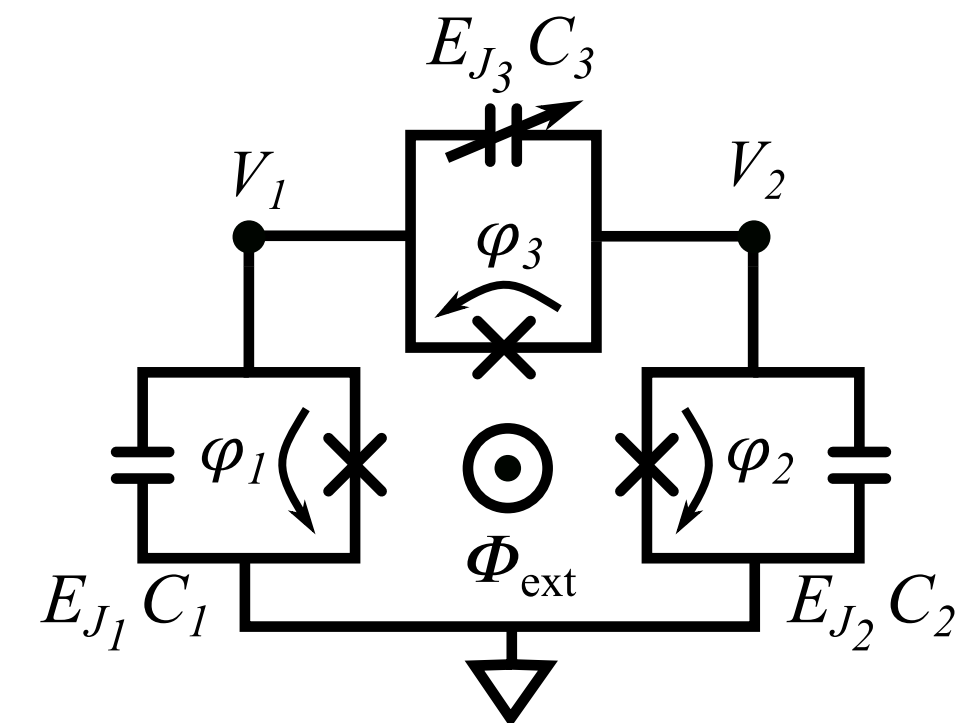
Capacitive Coupler
Terminal Labeling

Flux-tunable coupler¹



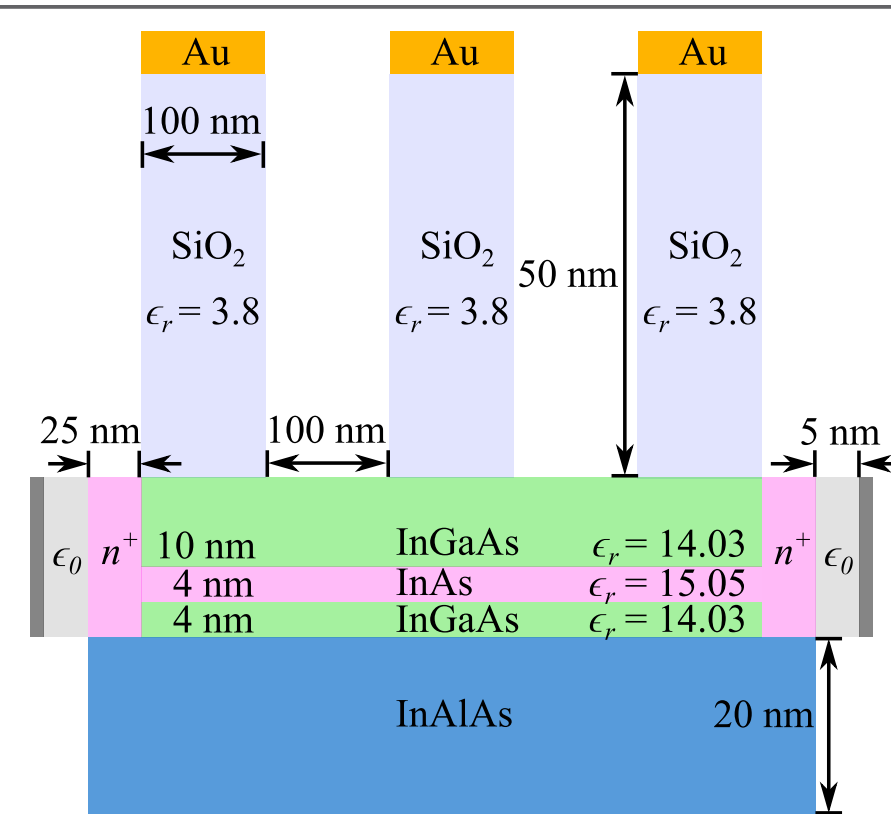
- 1st order sensitive to flux bias
- Current biases can heat system
- Cross-talk from stray magnetic fields
- + Compatible with cQED fab
- + Loss from distributed capacitors

¹ Adapted from J. Martinis, SQUnT 2020

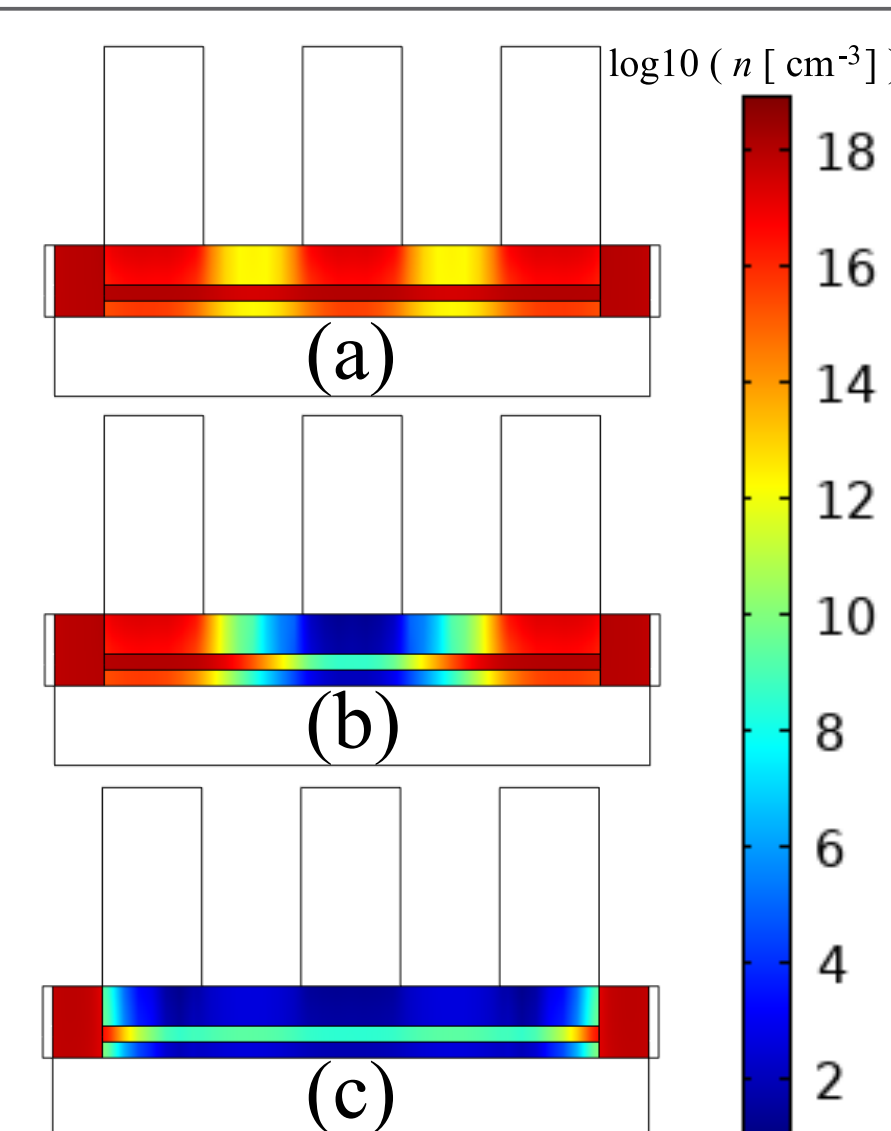


Tunable Coupler
Equivalent Circuit

Device Design & Semiconductor Simulations



Materials Stack

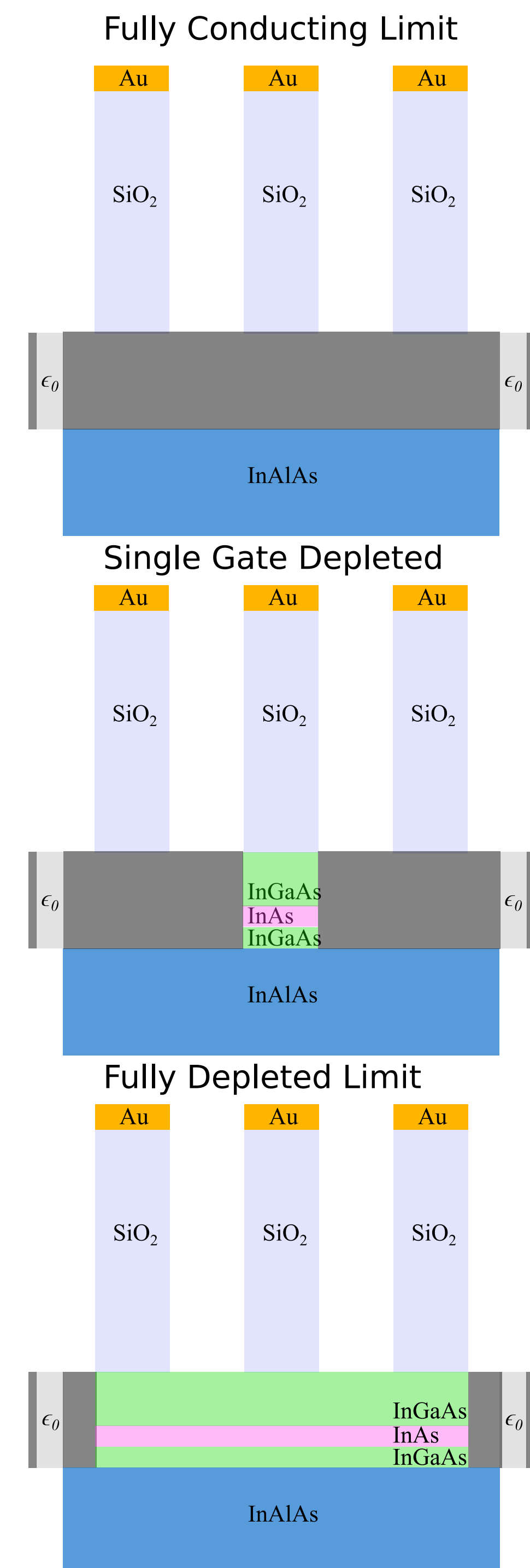


COMSOL Electron Densities

- ▶ III-V materials stack based on devices made by the Shabani group at NYU²
- ▶ Electron densities calculated from equilibrium solutions to the drift-diffusion equations with Fermi-Dirac statistics in COMSOL
- ▶ 2DEG confinement included with density gradients modifying the equilibrium electron densities³
- ▶ Electrostatic charge conservation applied to InAlAs, SiO₂, and air-gap dielectric regions
- ▶ Electron densities with gate biases (a) 0 V on all gates, (b) -3 V on center gate, 0 V on others, and -3 V on all three gates. Source bias set to 10 mV.
- ▶ End-to-end capacitance limited by air-gap capacitors (enlarged to reduce aspect ratio in COMSOL simulations)

² [Wickramasinghe et al., Applied Physics Letters **113**, 262104 (2018)]
³ [Ancona, Journal of Computational Electronics **10**, 65 (2011)]

Capacitance & Conductance Matrix Extraction



- ▶ Solve Poisson's equation with the charge continuity equation in 2D

$$-\nabla \cdot d(\epsilon_0 \nabla V - P) = \rho$$

- ▶ Extract Maxwell capacitance matrix

$$\begin{pmatrix} Q_1 \\ Q_2 \\ \vdots \\ Q_N \end{pmatrix} = \begin{pmatrix} C_{11} & C_{12} & \dots & C_{1N} \\ C_{21} & C_{22} & \dots & C_{2N} \\ \vdots & \vdots & \ddots & \vdots \\ C_{N1} & C_{N2} & \dots & C_{NN} \end{pmatrix} \begin{pmatrix} V_1 \\ V_2 \\ \vdots \\ V_N \end{pmatrix}$$

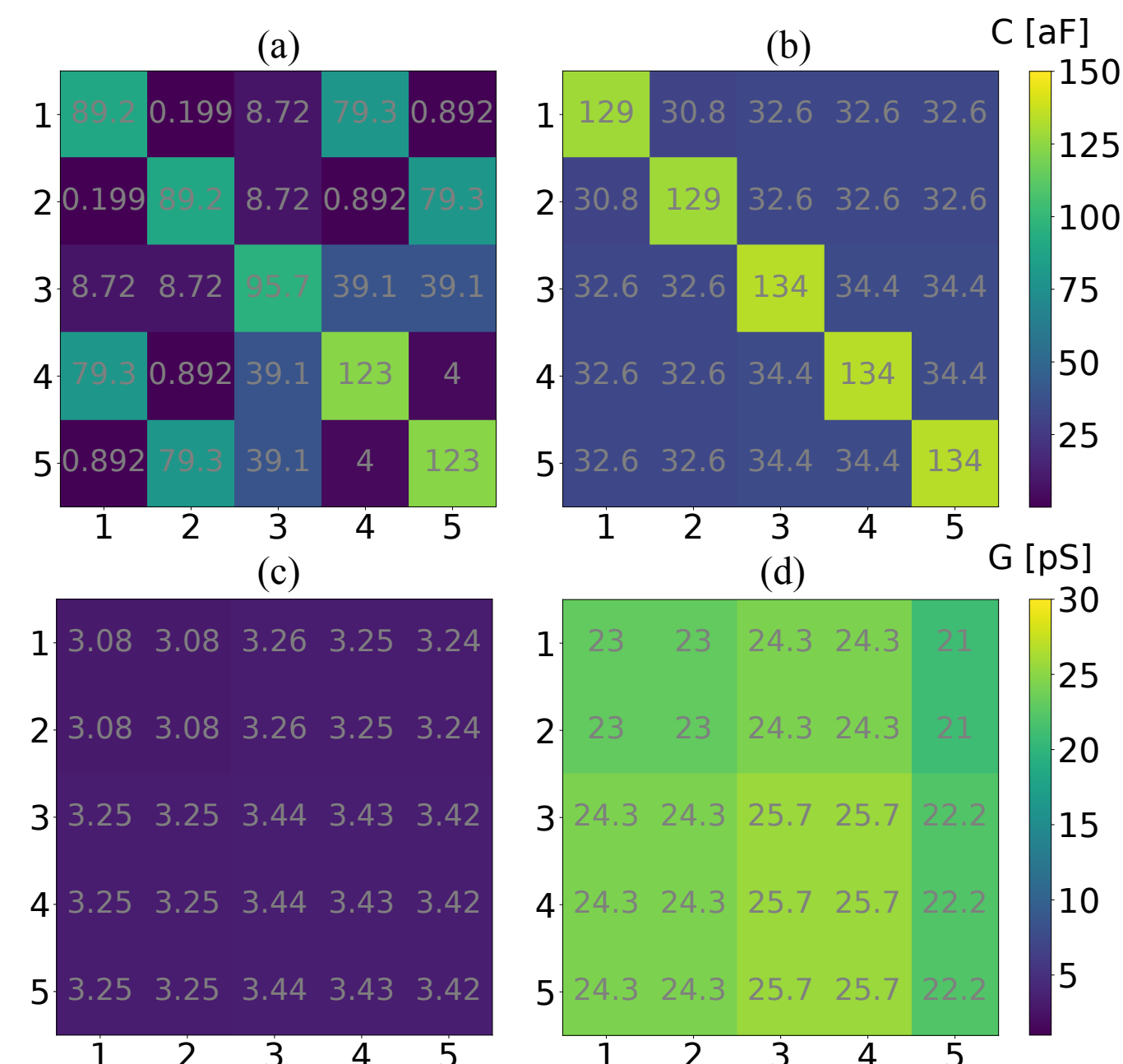
- ▶ Solve time harmonic equations

$$\nabla \cdot (\sigma \mathbf{E} + \mathbf{J}_e) + i\omega \rho = 0, \\ \nabla \cdot \mathbf{D} = \rho$$

- ▶ Use terminal current, voltage solutions to compute admittance matrix, Y

$$\begin{pmatrix} V_1 \\ V_2 \\ \vdots \\ V_N \end{pmatrix} = \begin{pmatrix} Y_{11} & Y_{12} & \dots & Y_{1N} \\ Y_{21} & Y_{22} & \dots & Y_{2N} \\ \vdots & \vdots & \ddots & \vdots \\ Y_{N1} & Y_{N2} & \dots & Y_{NN} \end{pmatrix} \begin{pmatrix} I_1 \\ I_2 \\ \vdots \\ I_N \end{pmatrix}$$

$$Y = G + i\omega C$$



Dielectric Loss Estimation

- ▶ Estimation of dielectric loss-limited T_1 ^{4,5}

$$T_1^{-1} = \frac{\omega}{Q} = \omega \sum_j \frac{p_j}{Q_j} + \Gamma_0$$

$$Q_j^{-1} = \tan \delta_j$$

$$p_j = \frac{t_j \epsilon_{1,j} \int_{S_j} |\mathbf{E}|^2 dS}{\int_V |\mathbf{E}|^2 dV}$$

- ▶ III-V loss tangents approximated with GaAs⁶

- ▶ Limited by SiO₂, pending measurement of III-Vs

⁴ [Wenner et al., Applied Physics Letters **99**, 113513 (2011)]

⁵ [Wang et al., Applied Physics Letters **107**, 162601 (2015)]

⁶ [McRae et al., arXiv e-prints, arXiv:2009.10101 (2020)]

⁷ [Li et al., IEEE Transactions on Applied Superconductivity **23**, 1501204 (2013)]

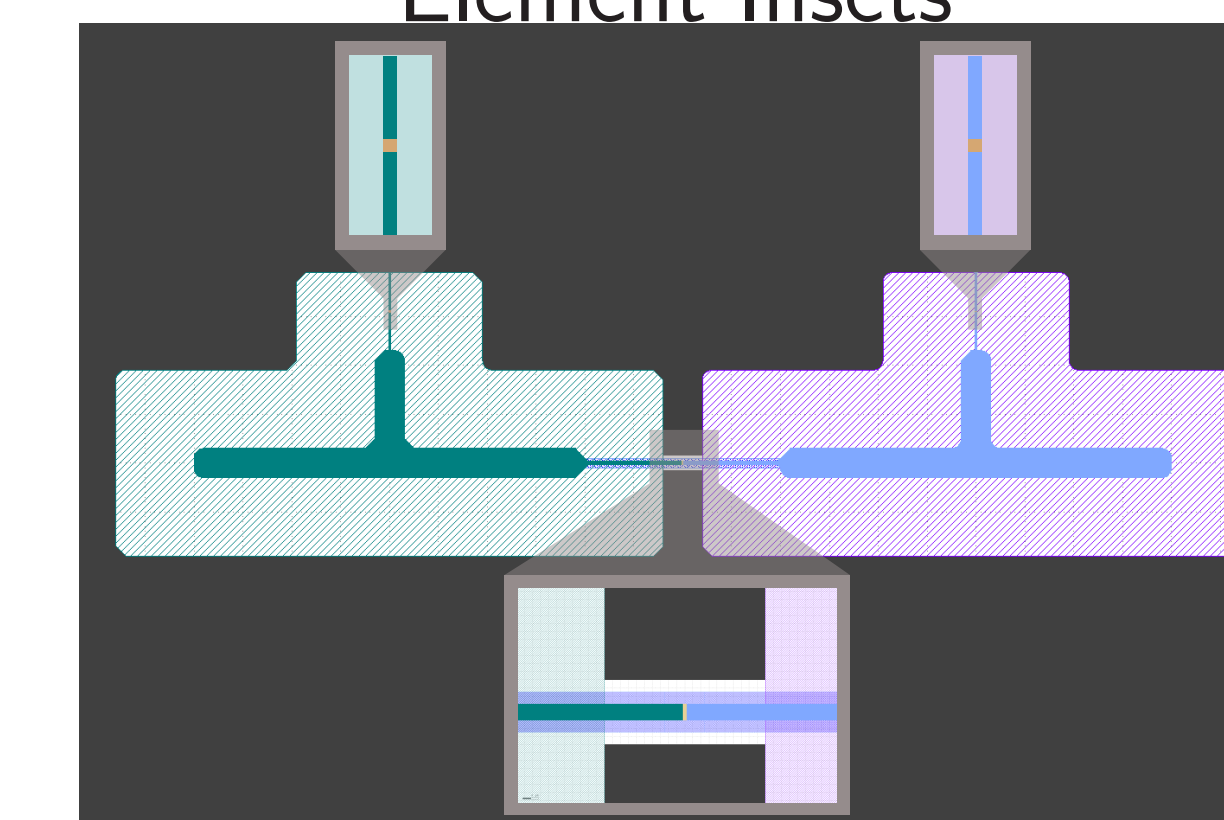
	t_j [nm]	p_j	$\tan \delta_j$	T_1 [μ s]
InGaAs	10	2.08E-5	4.8E-5	3190
InAs	4	3.18E-5	4.8E-5	20800
InGaAs	4	2.86E-5	4.8E-5	23200
InAlAs	20	5.64E-4	4.8E-5	1180
SiO ₂ ⁷	50	4.44E-3	2.00E-3	3.58
Total	-	-	-	3.57

EPR & Exchange Interaction Matrix Elements

EPR Matrix Elements

Mode No.	$\omega/2\pi$ [GHz]	Q	$\chi/2\pi$ [MHz]	
1 (d)	5.667	4.5E8	226	0.965
2 (d)	5.838	1.3E9	62.5	1.11
3 (d)	8.614	1.8E13	0.965	0.002
1 (c)	5.669	4.5E8	223	0.974
2 (c)	5.840	1.3E9	67.1	1.12
3 (c)	8.612	1.8E13	0.974	0.002

HFSS Model with Lumped Element Insets



- ▶ HFSS Eigenmodes \rightarrow EPR \rightarrow Matrix Elements^{8,9}

- ▶ Josephson junction inductances, capacitances as inputs
- ▶ Coupler modeled as lumped element capacitor

- ▶ Parametric sweep over the coupler capacitance to extract self- and cross-Kerr matrix elements

- ▶ Retain anharmonicities for exchange interaction matrix elements

- ▶ Extract exchange $Q_i Q_j$ interaction matrix elements $C^{-1}/2$ from^{10,11}

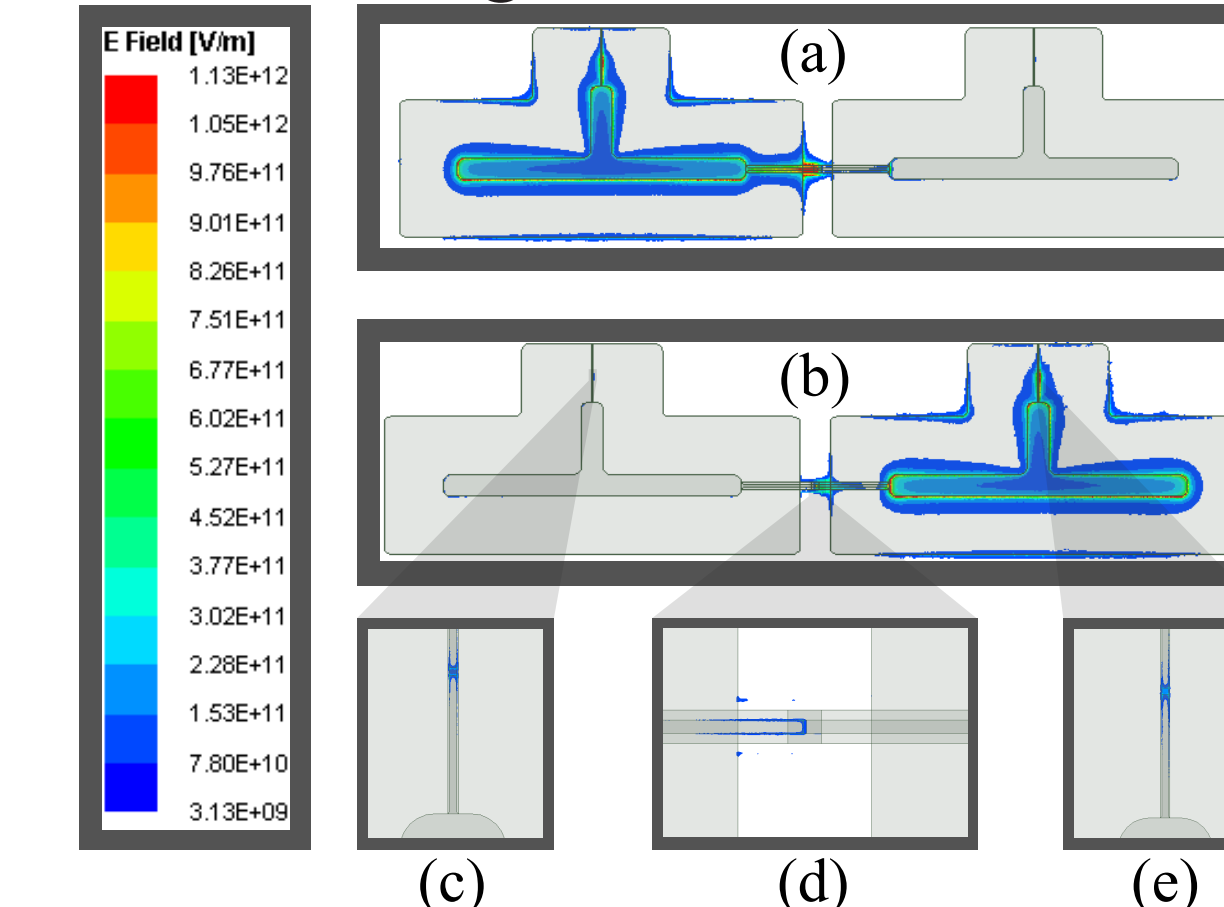
$$H = \frac{1}{2} Q^T C^{-1} Q + \sum_j E_j (1 - \cos \varphi_j)$$

$$C = \begin{pmatrix} C_1 + C_3 & -C_3 \\ -C_3 & C_2 + C_3 \end{pmatrix}$$

$$C_k = \frac{e^2}{2E_C} \approx -\frac{e^2}{2\alpha_k} = -\frac{e^2}{2\chi_{kk}}$$

- ▶ Exchange interaction matrix elements recover ≈ 160 on/off ratio

HFSS Eigenmode Solutions



Exchange Interaction Matrix Elements

Qubit Index	Matrix Elements [MHz]	
1 (d)	226	0.0005
2 (d)	0.0005	226
1 (c)	226	0.079
2 (c)	0.079	226

⁸ [Minev, arXiv e-prints, arXiv:1902.10355 (2019)]

⁹ [Minev et al., arXiv e-prints, arXiv:2010.00620 (2020)]

¹⁰ [Orlando et al., Phys. Rev. B **60**, 15398 (1999)]

¹¹ [Koch et al., Phys. Rev. A **76**, 042319 (2007)]

Future Work

- ▶ Finish experimental measurements of loss in III-V materials
- ▶ Begin testing tunable resonators with voltage-controlled III-V stack
- ▶ Fabricate and measure two qubits coupled by the III-V 2DEG coupler

Acknowledgements

We acknowledge funding from the Graduate Fellowship for STEM Diversity, NSF grant No. PHY-1653820, ARO grant No. W911NF-18-1-0125 and LPS/ARO grant No. W911NF-18-1-0115.